

# ABSTRACT

A power MOSFET 100 has a source metal 112 that contacts silicided source regions 114 through vias 160 etched in an insulating layer 200. The silicide layer 225 provides for a relatively small but highly conductive contact and thus reduces RDSON. The insulating material may be any suitable material including and not limited to one or a combination of materials such as BPSG, PSG, silicon dioxide and silicon nitride. The insulating layer is relatively thin and does not extend deeply into the gate trench,